



N-Channel 200 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	$DS(on)$ (Ω) I_D (A)	
200	0.053 at $V_{GS} = 15 \text{ V}$	36	57
	0.054 at V _{GS} = 10 V	36	57

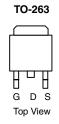
FEATURES

- TrenchFET® Power MOSFETs
- 175 °C Junction Temperature
- 100 % R_q and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

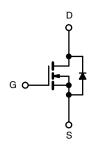


APPLICATIONS

- · Power Supply
- · Lighting Systems



Ordering Information: SUM36N20-54P-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	200	V	
Gate-Source Voltage		V _{GS}	± 25	∃	
Continuous Drain Current /T 175 °C\	T _C = 25 °C		36		
Continuous Drain Current (T _J = 175 °C)	T _C = 100 °C	I _D	22.6		
Pulsed Drain Current		I _{DM}	80	Α	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	20	1	
Single Pulse Avalanche Energy ^a	L = 0.111111	E _{AS}	20	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	D	166 ^b	w	
	$T_C = 25 ^{\circ}C$ $T_A = 25 ^{\circ}C^c$	$ P_D$	3.12	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	0.75]	

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR-4 material).

SUM36N20-54P

Vishay Siliconix



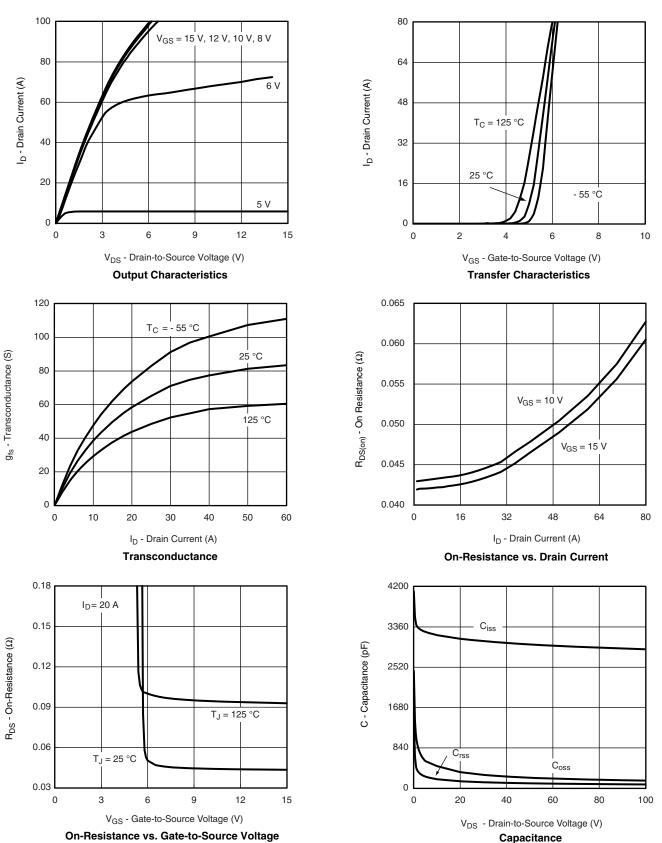
SPECIFICATIONS $T_J = 25$ °	C, unless o	therwise noted				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	200			V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5		4.5	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 25 \text{ V}$			± 300	
Zero Gate Voltage Drain Current		V _{DS} = 200 V, V _{GS} = 0 V			1	μΑ
	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V, T _J = 100 °C			25	
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 150 °C			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α
		$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		0.044	0.054	Ω
Drain-Source On-State Resistance ^a	_B	V _{GS} = 15 V, I _D = 20 A		0.0435	0.053	
Diani-Source On-State nesistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 100 °C			0.098	
		V _{GS} = 10 V, I _D = 20 A, T _J = 150 °C			0.130	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A	25			S
Dynamic ^b						
Input Capacitance	C _{iss}			3100		pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		300		
Reverse Transfer Capacitance	C _{rss}			135		
Total Cata Channel		$V_{DS} = 100 \text{ V}, V_{GS} = 15 \text{ V}, I_D = 50 \text{ A}$		85	127	
Total Gate Charge ^c	Q _g			57	85	0
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		14		nC
Gate-Drain Charge ^c	Q _{gd}			20		
Gate Resistance	R_{g}	f = 1 MHz		1.2	2	Ω
Turn-On Delay Time ^c	t _{d(on)}			16	25	- ns
Rise Time ^c	t _r	V_{DD} = 100 V, R_L = 2 Ω $I_D \cong 50$ A, V_{GEN} = 10 V, R_g = 1 Ω		170	260	
Turn-Off Delay Time ^c	t _{d(off)}			27	42	
Fall Time ^c	t _f			9	18	
Source-Drain Diode Ratings and Cha	aracteristics	r _C = 25 °C ^b				
Continuous Current	I _S				36	۸
Pulsed Current	I _{SM}				80	Α
Forward Voltage ^a	V _{SD}	I _F = 20 A, V _{GS} = 0 V		0.86	1.5	V
Reverse Recovery Time	t _{rr}			116	175	ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = 40 A, dl/dt = 100 A/μs		9	14	Α
Reverse Recovery Charge	Q _{rr}			0.53	0.8	μC
Reverse Recovery Fall Time	t _a			84		nS
Reverse Recovery Rise Time	t _b			32		

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



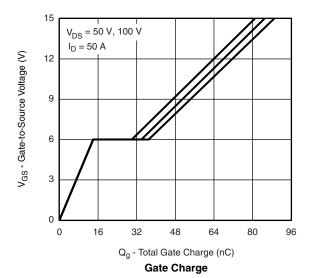
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

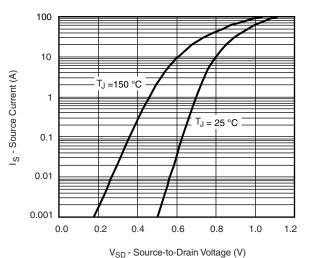


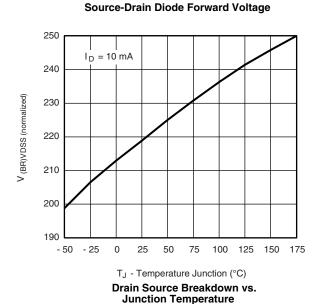
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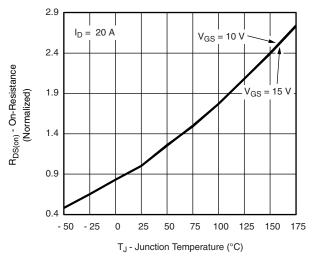
VISHAY

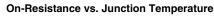
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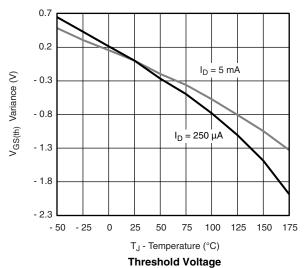


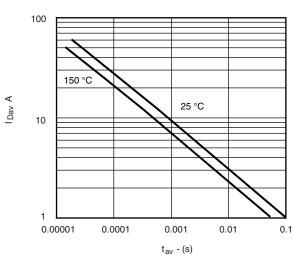










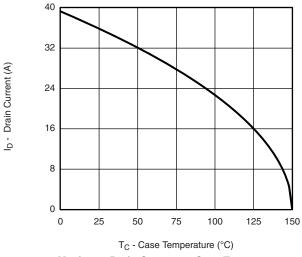


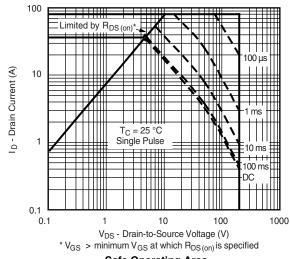
Single Pulse Avalanche Current Capability vs. Time



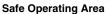
Normalized Effective Transient Thermal Impedance

THERMAL RATINGS





Maximum Drain Curent vs. Case Temperature





Normalized Thermal Transient Impedance, Junction-to-Case

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